

Technical Sessions At-a-Glance

Wednesday December 7, 2011

12:00 - 7:00 PM	<i>Registration - Grand Ballroom Lounge</i>					
Room	Colony Ballroom	Charles Carroll Room	Benjamin Banneker Room	Juan Ramon Jimenez Room	Margaret Brent Room	Prince Georges Room
1:30–3:30 PM	WP1: Nanoelectronics I: Novel Devices	WP2: Wide Bandgap I: UV Emitters	WP3: Oxides and Dielectrics	WP4: Photovoltaics/Electronics for Energy	WP5: Optics and Optoelectronics	
3:45–5:45 PM	WP6: Nanoelectronics II: 2D Materials and Memory	WP7: Wide Bandgap II: Nitride Optoelectronics	WP8: Oxides and Dielectrics II	WP9: Organic Materials and Devices	WP10: Novel Devices I	
6:00–8:30 PM	<i>Welcome Reception and Poster Session - Grand Ballroom</i>					

Thursday December 8, 2011

7:30 AM - 5:00 PM	<i>Registration - Grand Ballroom Lounge</i>					
8:30–10:15 AM	<i>Plenary Session - Colony Ballroom</i> <i>James Speck, University of California, Progress in Nonpolar and Semipolar GaN Materials and Devices</i> <i>H.-S. Philip Wong, Stanford University, Emerging Memory Devices</i>					
Room	Colony Ballroom	Charles Carroll Room	Benjamin Banneker Room	Juan Ramon Jimenez Room	Margaret Brent Room	Prince Georges Room
10:45 AM –12:15 PM	TA1: Nanoelectronics III	TA2: Wide Bandgap III: Device Physics and Characterization	TA3: Sensors, NEMS, and MEMS	TA4: Flexible Electronics	TA5: Processing Technology	
12:15-1:15 PM	<i>Lunch - Grand Ballroom</i>					
1:15–3:15 PM	TP1: Nanoelectronics IV	TP2: Wide Bandgap IV: Wide Bandgap Materials for Optoelectronics	TP3: Sensors	TP4: SOI and SiGe	TP5: Testing and Characterization	TP10: Reliability*
3:45–6:05 PM	TP6: Nanoelectronics V: Nanotubes and Graphene	TP7: Wide Bandgap V: GaN/ZnO Materials and Devices	TP8: Low Power Electronics	TP9: SiGe and Germanium		(*Note: TP10 is intentionally out of order due to limited space availability)
6:15–8:30 PM	<i>Symposium Awards Banquet - Grand Ballroom</i>					

Friday December 9, 2011

Room	Colony Ballroom	Charles Carroll Room	Benjamin Banneker Room	Juan Ramon Jimenez Room	Margaret Brent Room	Prince Georges Room
8:00 – 10:00 AM	FA1: Nanoelectronics VI: Nanotubes and Graphene	FA2: Wide Bandgap VI: SiC Materials and Devices	FA3: Nanowires, Assembly Methods and Devices I	FA4: Modeling & Simulation I		
10:15 AM – 12:25 PM	FA5: Nanoelectronics VII: Nanotubes and Graphene	FA6: Wide Bandgap VII: III-Nitride HEMTs	FA7: Nanowires, Assembly Methods and Devices II	FA8: Modeling & Simulation II		
12:25-1:15 PM	<i>Lunch (on your own)</i>					
1:15–3:15 PM	FP1: Optics, Optoelectronics and Plasmonics	FP2: Space and Extreme Environment Electronics	FP3: Novel Devices II	FP4: Modeling & Simulation III		